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IPD60R3K4CEAUMA1

IPD60R3K4CEAUMA1 Information

Part Number IPD60R3K4CEAUMA1 Manufacturer Infineon Technologies

Discrete Semiconductor Products Category

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH TO-252-3

Package TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com For Reference Only

E-mail: salesdept@heisener.com



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IPD60R3K4CEAUMA1 Specifications

Manufacturer Part Number IPD60R3K4CEAUMA1 Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 2.6A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 40μA Gate Charge (Qg) (Max) @ Vgs 4.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 93pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 29W (Tc) Rds On (Max) @ Id, Vgs 3.4 Ohm @ 500mA, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-T0252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63 Report errors?		
Category Discrete Semiconductor Products Fackage TO-252-3, DPak (2 Leads + Tab), SC-63 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 2.6A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 40μA Gate Charge (Qg) (Max) @ Vgs 4.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 93pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 29W (Tc) Rds On (Max) @ Id, Vgs 3.4 Ohm @ 500mA, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Manufacturer Part Number	IPD60R3K4CEAUMA1
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FET Type Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 40°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case N-Channel N-Channel N-Channel NOSFET (Metal Oxide) 800 V 805 V 805 V 264 (Tc) 10V 467 0 10V 93pF @ 100V 460 C 210V 940 C 210V 950 C (TJ)	Package	TO-252-3, DPak (2 Leads + Tab), SC-63
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C2.6A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.5V @ 40μAGate Charge (Qg) (Max) @ Vgs4.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds93pF @ 100VVgs (Max)±20VFET Feature-Power Dissipation (Max)29W (Tc)Rds On (Max) @ Id, Vgs3.4 Ohm @ 500mA, 10VOperating Temperature-40°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO252-3Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Series	-
Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C2.6A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.5V @ 40μAGate Charge (Qg) (Max) @ Vgs4.6nC @ 10VInput Capacitance (Ciss) (Max) @ Vds93pF @ 100VVgs (Max)±20VFET Feature-Power Dissipation (Max)29W (Tc)Rds On (Max) @ Id, Vgs3.4 Ohm @ 500mA, 10VOperating Temperature-40°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO252-3Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 40µA Gate Charge (Qg) (Max) @ Vgs 4.6nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 93pF @ 100V Vgs (Max) +20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.4 Ohm @ 500mA, 10V Operating Temperature 40°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 3.5V @ 40μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.4 Ohm @ 500mA, 10V Operating Temperature 40°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	650V
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Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 93pF @ 100V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3.4 Ohm @ 500mA, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) #20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-T0252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	3.5V @ 40μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)29W (Tc)Rds On (Max) @ Id, Vgs3.4 Ohm @ 500mA, 10VOperating Temperature-40°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO252-3Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Gate Charge (Qg) (Max) @ Vgs	4.6nC @ 10V
FET Feature - Power Dissipation (Max) 29W (Tc) Rds On (Max) @ Id, Vgs 3.4 Ohm @ 500mA, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	93pF @ 100V
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Rds On (Max) @ Id, Vgs3.4 Ohm @ 500mA, 10VOperating Temperature-40°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO252-3Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Surface Mount PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	29W (Tc)
Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	3.4 Ohm @ 500mA, 10V
Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-40°C ~ 150°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	PG-TO252-3
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

IPD60R3K4CEAUMA1 Guarantees



Ouality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPD60R3K4CEAUMA1 Payment Methods





















IPD60R3K4CEAUMA1 Shipping Methods













If you have any question about IPD60R3K4CEAUMA1, please do not hesitate to contact us!

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